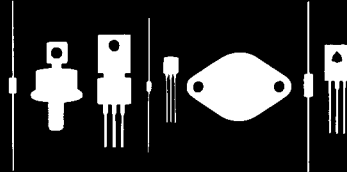


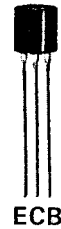
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145 Adams Avenue
Hauppauge, New York 11788



2N3707
2N3708
2N3709
2N3710
2N3711

SILICON NPN TRANSISTOR



JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3707 Series types are Molded Epoxy Silicon NPN Transistors designed for low level, low noise (2N3707) and Low level, high gain (2N3708, 2N3709, 2N3710, 2N3711) applications. Recommended PNP complementary series is 2N4058 thru 2N4062.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNIT
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CE0}	30	V
Emitter-Base Voltage	V _{EB0}	6.0	V
Collector Current	I _C	200	mA
Power Dissipation	PD	625	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 TO +150°C	°C

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$)

SYMBOL	TEST CONDITIONS	2N3707		2N3708		2N3709		2N3710		2N3711		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
I _{CB0}	V _{CB} =20V		100		100		100		100		100	nA
I _{EB0}	V _{EB} =6.0V		100		100		100		100		100	nA
BV _{CEO}	I _C =1.0mA	30		30		30		30		30		V
V _{CE(SAT)}	I _C =10mA, I _B =0.5mA		1.0		1.0		1.0		1.0		1.0	V
V _{BE(ON)}	V _{CE} =5.0V, I _C =1.0mA	0.5	1.0	0.5	1.0	0.5	1.0	0.5	1.0	0.5	1.0	V
h _{FE}	V _{CE} =5.0V, I _C =100μA	100	400									
h _{FE}	V _{CE} =5.0V, I _C =1.0mA			45	660	45	165	90	330	180	660	
h _{fe}	V _{CE} =5.0V, I _C =100μA f=1kHz	100	550									
h _{fe}	V _{CE} =5.0V, I _C =1.0mA f=1kHz			45	800	45	250	90	450	180	800	
NF	V _{CE} =5.0V, I _C =100μA, R _G =10KΩ, BW=15.7kHz (2N3707 only)		5.0		-		-		-		-	dB

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